

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOS)

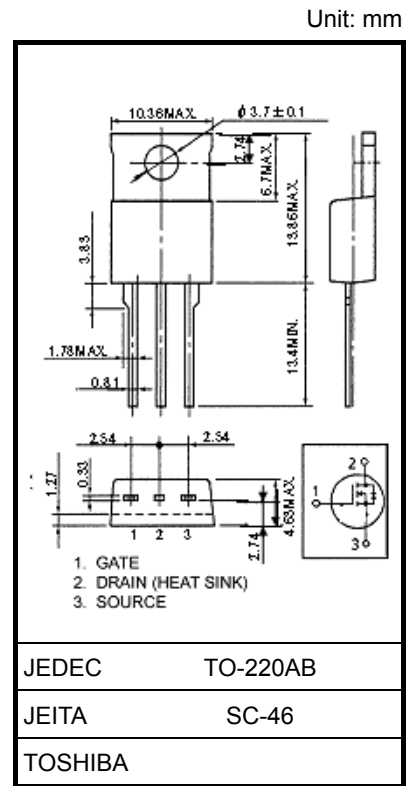
TK80E08K3

■ E-Bike/UPS/Inverter

- Low drain-source ON resistance : $R_{DS(ON)} = 7.5 \text{ m}\Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 135 \text{ S}$ (typ.)
- Low leakage current : $I_{DSS} = 10 \text{ }\mu\text{A}$ (max) ($V_{DS} = 75 \text{ V}$)
- Enhancement mode : $V_{th} = 2.0\sim 4.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	75	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	75	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	80	A
	DC (Note 1,4)	I_D	70	A
	Pulse (Note 1)	I_{DP}	240	A
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	200	W
Single pulse avalanche energy (Note 2)		E_{AS}	107	mJ
Avalanche current		I_{AR}	40	A
Repetitive avalanche energy (Note 3)		E_{AR}	20	mJ
Peak diode recovery dv/dt (Note 5)		dv/dt	12	V/ns
Channel temperature (Note 4)		T_{ch}	175	$^\circ\text{C}$
Storage temperature range (Note 4)		T_{stg}	-55~175	$^\circ\text{C}$



Note :Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
 Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc). Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.75	$^\circ\text{C} / \text{W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	83.3	$^\circ\text{C} / \text{W}$

- Note 1: Ensure that the channel temperature does not exceed 175°C.
- Note 2: $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 100 \text{ }\mu\text{H}$, $R_G = 25 \text{ }\Omega$, $I_{AR} = 40\text{A}$
- Note 3: Repetitive rating: pulse width limited by maximum channel temperature
- Note 4: $T_c=100$
- Note 5: $I_{DR} = 80\text{A}$, $di/dt = 160\text{A}/\mu\text{s}$, $T_{ch} = T_{ch \text{ max}}$.

This transistor is an electrostatic-sensitive device.
 Please handle with caution.

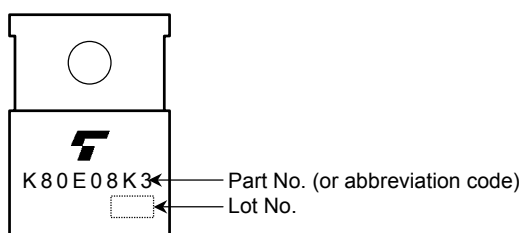
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 1	μA
Drain cut-off current		I_{DSS}	$V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	75	—	—	V
		$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	45	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$	—	7.5	9.0	$\text{m}\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 40\text{ A}$	67	135	—	S
Input capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	3600	—	pF
Reverse transfer capacitance		C_{rss}		—	350	—	
Output capacitance		C_{oss}		—	500	—	
Switching time	Rise time	t_r		—	95	—	ns
	Turn-on time	t_{on}		—	135	—	
	Fall time	t_f		—	85	—	
	Turn-off time	t_{off}		Duty $\leq 1\%$, $t_w = 10\ \mu\text{s}$	—	220	
Total gate charge (Gate-source plus gate-drain)		Q_g	$V_{DD} \approx 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 80\text{ A}$	—	75	—	nC
Gate-source charge		Q_{gs}		—	44	—	
Gate-drain ("miller") charge		Q_{gd}		—	31	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	80	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	240	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 80\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.5	V
Reverse recovery time	t_{rr}	$I_{DR} = 80\text{ A}, V_{GS} = 0\text{ V}$	—	45	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR} / dt = 100\text{ A} / \mu\text{s}$	—	72	—	μC

Marking



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